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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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↓	6,087,225	07/11/2000	Bronner, G.B., et al.	438	275	02/05/98
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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OTHER DOCUMENTS

Including Abstracts, Tables, Figures, Pertinent Papers, Etc.

**Examiner Initial	
PP	Chen, Y., et al., "Performance and Reliability Assessment of Dual-Gate CMOS Devices with Gate Oxide Grown Nitrogen Implanted Si Substrates", <u>International Electron Device Meeting</u> , pg. 1-4, (1997)
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Examiner:

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